

Sub D1
C1
C2

43. (Amended) A method of manufacturing a display device comprising the steps of:
forming a thin film transistor over a substrate;
forming a pixel electrode electrically connected to the thin film transistor;
forming a body with a textured surface on the pixel electrode;
forming a light reflection film on the body with the textured surface by one selected from
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method;
and
flattening a surface of the light reflection film by a CMP process.

Sub D3
C2

50. (Amended) A method of manufacturing a display device comprising the steps of:
forming a thin film transistor over a substrate;
forming a pixel electrode electrically connected to the thin film transistor;
forming a body with a textured surface on the pixel electrode; and
forming a light reflection film on the body with the textured surface by one selected from
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method,
wherein the light reflection film has a higher refractive index than the body with the textured
surface.

Sub D4
C3

57. (Amended) A method of manufacturing a display device comprising the steps of:
forming an insulated gate field effect transistor on a semiconductor substrate;
forming a pixel electrode electrically connected to the insulated gate field effect transistor;
forming a body with a textured surface on the pixel electrode; and
forming a light reflection film on the body with the textured surface by one selected from
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

D4
C3
cont

64. (Amended) A method of manufacturing a display device comprising the steps of:
forming an insulated gate field effect transistor on a semiconductor substrate;
forming a pixel electrode electrically connected to the insulated gate field effect transistor;
forming a body with a textured surface on the pixel electrode;
forming a light reflection film on the body with the textured surface by one selected from
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method;
and
flattening a surface of the light reflection film by a CMP process.

Sub D6
C4

71. (Amended) A method of manufacturing a display device comprising the steps of:
forming an insulated gate field effect transistor on a semiconductor substrate;
forming a pixel electrode electrically connected to the insulated gate field effect transistor;
forming a body with a textured surface on the pixel electrode; and
forming a light reflection film on the body with the textured surface by one selected from
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method,
wherein the light reflection film has a higher refractive index than the body with the textured
surface.

REMARKS

In the Office Action, the Examiner rejects Claims 36-77 under the judicially created doctrine of double patenting over claims 1-81 of Application serial no. 09/329,597 (now U.S. Patent 6,384,886, a copy which is enclosed herewith). This rejection is respectfully traversed.

Applicants have now amended each of the independent claims pending in this application to include the limitation of "forming a light reflection film on the body with the textured surface by